

Automotive-grade 450 V internally clamped IGBT E_{SCIS} 300 mJ

Datasheet - production data

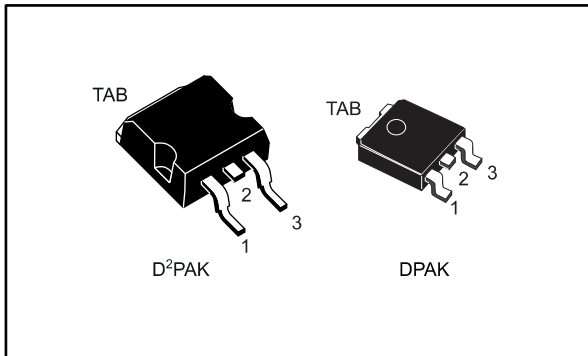
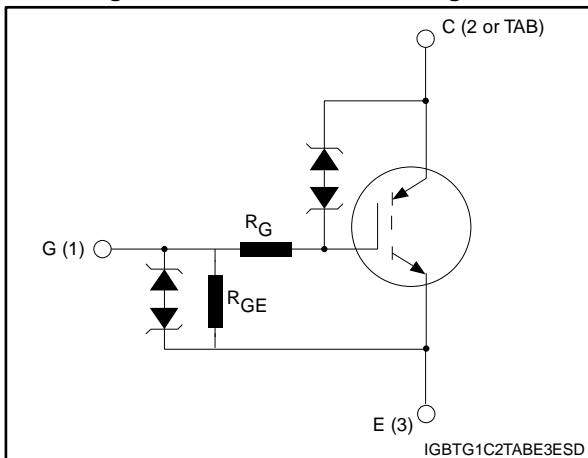



Figure 1: Internal schematic diagram



Features

- AEC-Q101 qualified 
- SCIS energy of 300 mJ @ T_J = 25 °C
- Parts are 100% tested in SCIS
- ESD gate-emitter protection
- Gate-collector high voltage clamping
- Logic level gate drive
- Very low saturation voltage
- High pulsed current capability
- Gate and gate-emitter resistor

Applications

- Automotive ignition coil driver circuit

Description

This application-specific IGBT utilizes the most advanced PowerMESH™ technology optimized for coil driving in the harsh environment of automotive ignition systems. These devices show very low on-state voltage and very high SCIS energy capability over a wide operating temperature range. Moreover, ESD-protected logic level gate input and an integrated gate resistor means no external protection circuitry is required.

Table 1: Device summary

| Order code | Marking | Package | Packing |
|---------------|-----------|--------------------|---------------|
| STGB20N45LZAG | GB20N45LZ | D ² PAK | Tape and reel |
| STGD20N45LZAG | GD20N45LZ | DPAK | |

Contents

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1 Electrical ratings

Table 2: Absolute maximum ratings

| Symbol | Parameter | Value | | Unit |
|--------------------------------------|--|---------------------------|------|------|
| | | D ² PAK | DPAK | |
| V _{CES} | Collector-emitter voltage (V _{GE} = 0 V) | V _{CES(clamped)} | | V |
| V _{ECS} | Emitter-collector voltage (V _{GE} = 0 V) | 20 | | V |
| I _C | Continuous collector current at T _C = 25 °C, V _{GE} = 4 V | 25 | | A |
| | Continuous collector current at T _C = 100 °C, V _{GE} = 4 V | 25 | | A |
| I _{CP} ⁽¹⁾ | Pulsed collector current | 50 | | A |
| V _{GE} | Gate-emitter voltage | V _{GE(clamped)} | | V |
| P _{TOT} | Total dissipation at T _C = 25 °C | 150 | 125 | W |
| E _{SCIS_25} ⁽²⁾ | Self-clamping inductive switching energy | 300 | | mJ |
| E _{SCIS_150} ⁽³⁾ | Self-clamping inductive switching energy @ T _J = 150 °C | 170 | | mJ |
| ESD | Human body model, R = 1.5 kΩ, C = 100 pF | 4 | | kV |
| | Charged device model | 2 | | kV |
| T _{STG} | Storage temperature range | -55 to 175 | | °C |
| T _J | Operating junction temperature range | | | |

Notes:

⁽¹⁾Pulse width limited by maximum junction temperature.

⁽²⁾Starting T_J = 25 °C, L = 3 mH, R_g = 1 kΩ, V_{cc} = 50 V during inductor charging and V_{cc} = 0 V during the time in clamp. Parts are 100% electrically tested in production.

⁽³⁾Starting T_J = 150 °C, L = 3 mH, R_g = 1 kΩ, V_{cc} = 50 V during inductor charging and V_{cc} = 0 V during the time in clamp.

Table 3: Thermal data

| Symbol | Parameter | Value | | Unit |
|-----------------------|-------------------------------------|--------------------|------|------|
| | | D ² PAK | DPAK | |
| R _{thj-case} | Thermal resistance junction-case | 1 | 1.2 | °C/W |
| R _{thj-amb} | Thermal resistance junction-ambient | 62.5 | 100 | °C/W |

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 4: Static characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------------------|--------------------------------------|---|------|------|------|------------------|
| $V_{CES(\text{clamped})}$ | Collector-emitter clamped voltage | $I_C = 2\text{ mA}, V_{GE} = 0\text{ V}$ | | 450 | | V |
| | | $I_C = 2\text{ mA}, V_{GE} = 0\text{ V}, T_J = -40\text{ °C to }175\text{ °C}$ | 415 | | 475 | V |
| $V_{(BR)ECS}$ | Emitter-collector break-down voltage | $I_C = 75\text{ mA}, V_{GE} = 0\text{ V}$ | 20 | | | V |
| $V_{GE(\text{clamped})}$ | Gate-emitter clamped voltage | $I_G = \pm 2\text{ mA}, T_J = -40\text{ °C to }175\text{ °C}$ | 12 | | 16 | V |
| $V_{CE(\text{sat})}$ | Collector-emitter saturation voltage | $V_{GE} = 4\text{ V}, I_C = 6\text{ A}$ | | 1.1 | 1.25 | V |
| | | $V_{GE} = 4.5\text{ V}, I_C = 10\text{ A}, T_J = 175\text{ °C}$ | | 1.25 | 1.55 | V |
| $V_{GE(\text{th})}$ | Gate-threshold voltage | $V_{GE} = V_{CE}, I_C = 1\text{ mA}$ | | 1.65 | | V |
| | | $V_{GE} = V_{CE}, I_C = 1\text{ mA}, T_J = 175\text{ °C}$ | | 1.05 | | V |
| I_{CES} | Collector cut-off current | $V_{CE} = 15\text{ V}, V_{GE} = 0\text{ V}, T_J = 150\text{ °C}$ | | | 20 | μA |
| | | $V_{CE} = 200\text{ V}, V_{GE} = 0\text{ V}, T_J = 150\text{ °C}$ | | | 100 | μA |
| I_{GES} | Gate-emitter leakage current | $V_{GE} = \pm 10\text{ V}, V_{CE} = 0\text{ V}$ | | 625 | | μA |
| | | $V_{GE} = \pm 10\text{ V}, V_{CE} = 0\text{ V}, T_J = -40\text{ °C to }175\text{ °C}$ | 450 | | 900 | μA |
| R_{GE} | Gate emitter resistance | | 11 | 16 | 22 | $\text{k}\Omega$ |
| R_G | Gate resistance | | | 120 | | Ω |

Table 5: Dynamic characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|--|------|------|------|-------------|
| C_{ies} | Input capacitance | $V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0\text{ V}$ | - | 1011 | - | pF |
| C_{oes} | Output capacitance | | - | 87 | - | |
| C_{res} | Reverse transfer capacitance | | - | 14 | - | |
| Q_g | Total gate charge | $V_{CE} = 13\text{ V}, I_C = 10\text{ A}, V_{GE} = 0\text{ to }5\text{ V}$ | - | 26 | - | nC |

Table 6: Resistive load switching characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------|--------------------|---|------|------|------|---------------|
| $t_{d(on)}$ | Turn-on delay time | $V_{CC} = 14\text{ V}$, $V_{GE} = 5\text{ V}$, $R_L = 1\ \Omega$, $R_G = 1\text{ k}\Omega$ (see Figure 18: "Test circuit for resistive load switching") | - | 1.1 | - | μs |
| t_r | Rise time | | - | 3.6 | - | μs |
| $t_{d(on)}$ | Turn-on delay time | $V_{CC} = 14\text{ V}$, $V_{GE} = 5\text{ V}$, $R_L = 1\ \Omega$, $R_G = 1\text{ k}\Omega$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 18: "Test circuit for resistive load switching") | - | 1.06 | - | μs |
| t_r | Rise time | | - | 3.5 | - | μs |

Table 7: Inductive load switching characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|------------------------|--|------|------|------|------------------|
| $t_{d(off)}$ | Turn-off delay time | $V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$, $I_C = 10\text{ A}$, $V_{GE} = 5\text{ V}$, $R_G = 1\text{ k}\Omega$ (see Figure 17: "Test circuit for inductive load switching") | - | 4.6 | - | μs |
| t_f | Fall time | | - | 8.4 | - | μs |
| dV/dt | Turn-off voltage slope | | - | 165 | - | V/ μs |
| $t_{d(off)}$ | Turn-off delay time | $V_{CC} = 300\text{ V}$, $L = 1\text{ mH}$, $I_C = 10\text{ A}$, $V_{GE} = 5\text{ V}$, $R_G = 1\text{ k}\Omega$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 17: "Test circuit for inductive load switching") | - | 4.7 | - | μs |
| t_f | Fall time | | - | 9.8 | - | μs |
| dV/dt | Turn-off voltage slope | | - | 116 | - | V/ μs |

2.1 Electrical characteristics (curves)

Figure 2: $V_{CE(sat)}$ vs junction temperature ($I_c = 6.0\text{ A}$)

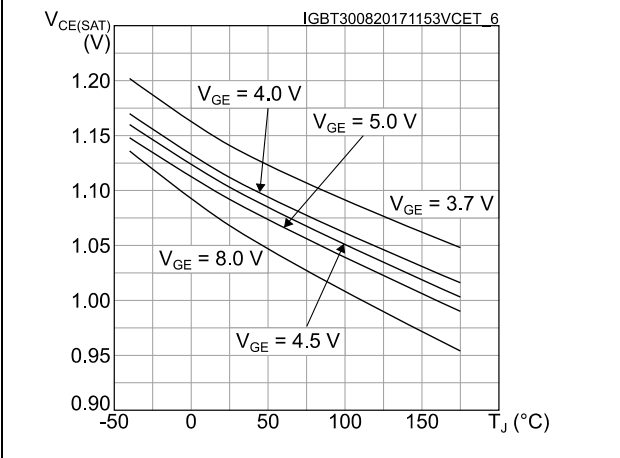


Figure 3: $V_{CE(sat)}$ vs junction temperature ($I_c = 10.0\text{ A}$)

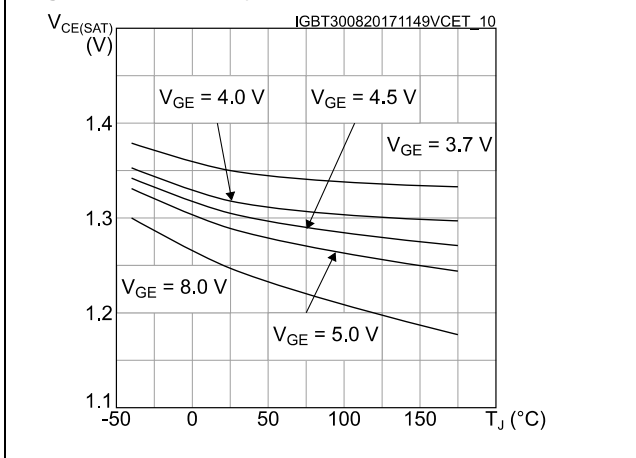


Figure 4: Self-clamped inductive switching current vs inductance

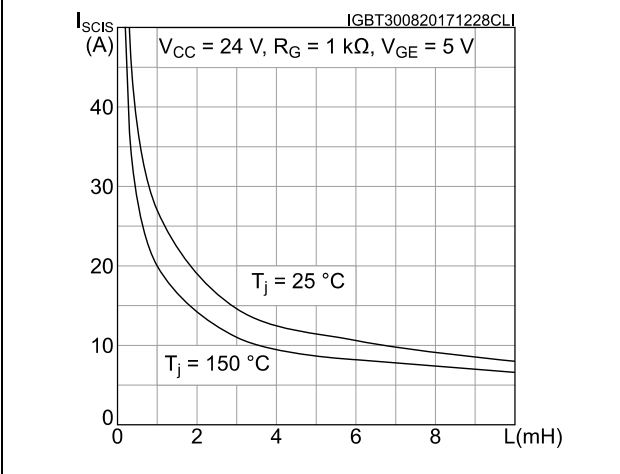


Figure 5: Output characteristics ($T_j = 25\text{ °C}$)

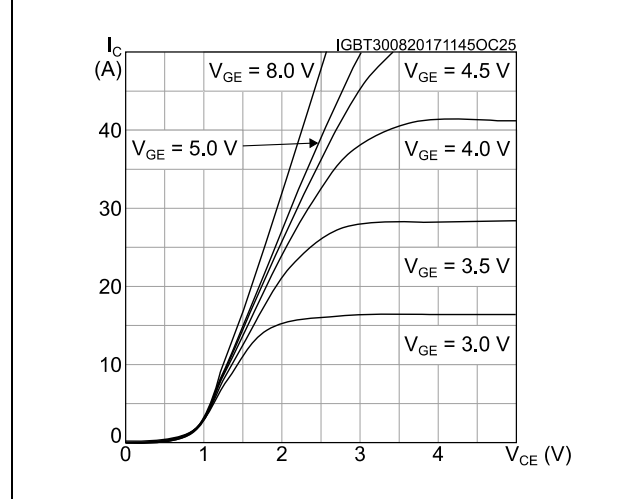


Figure 6: Output characteristics ($T_j = -40\text{ °C}$)

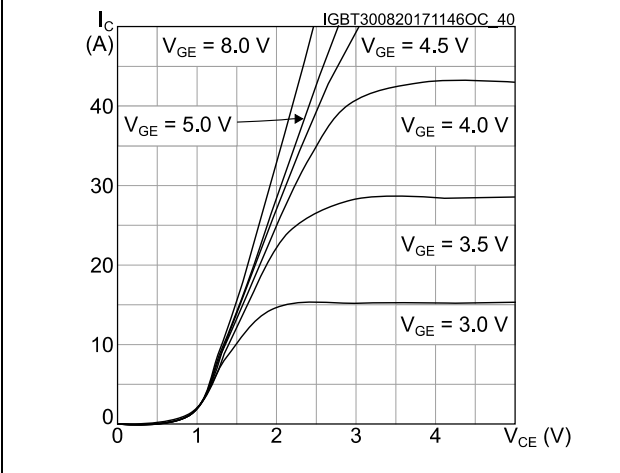
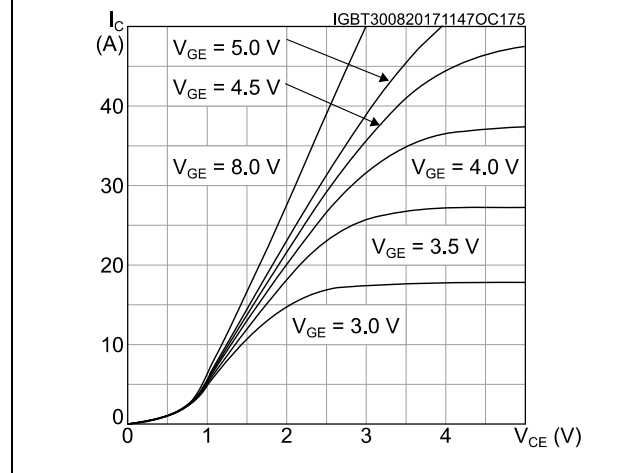
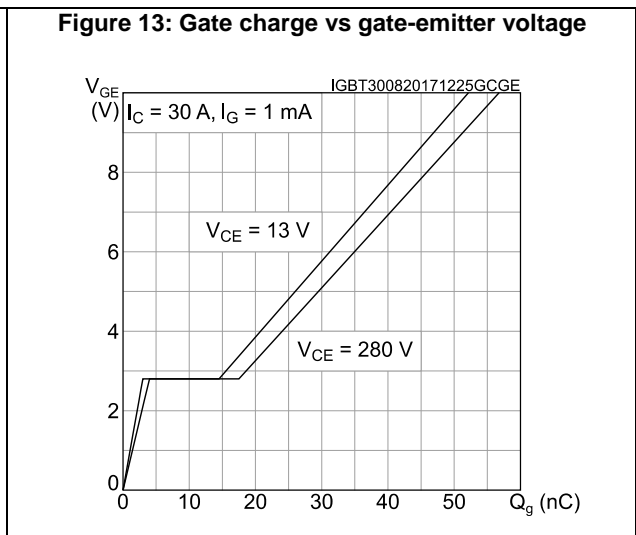
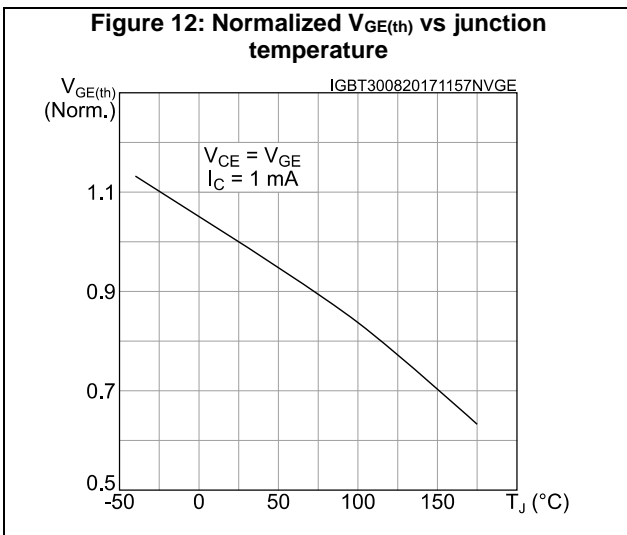
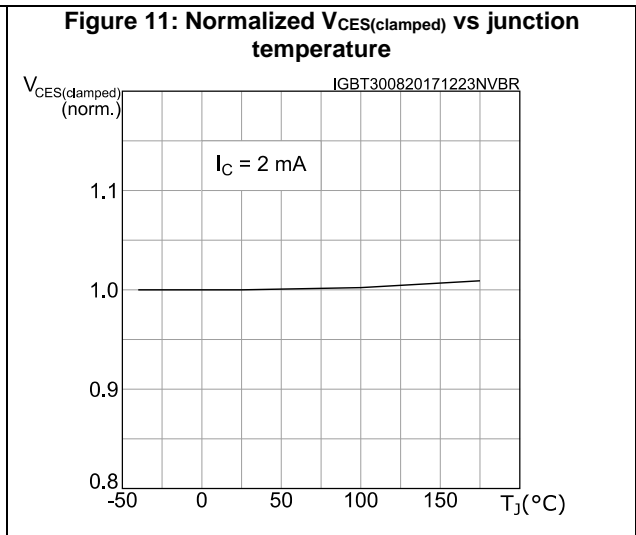
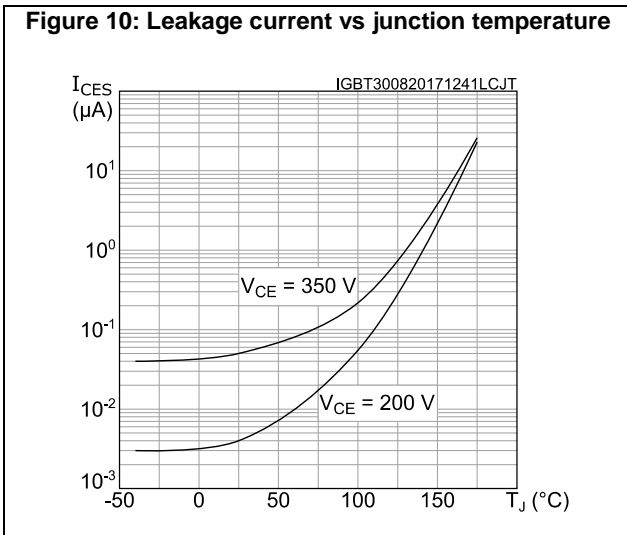
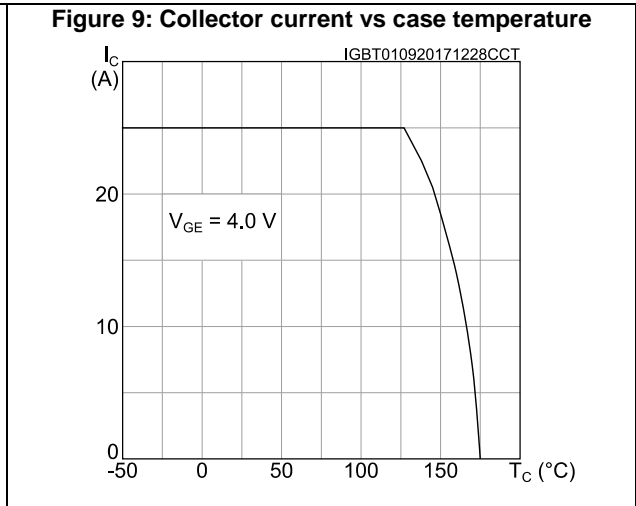
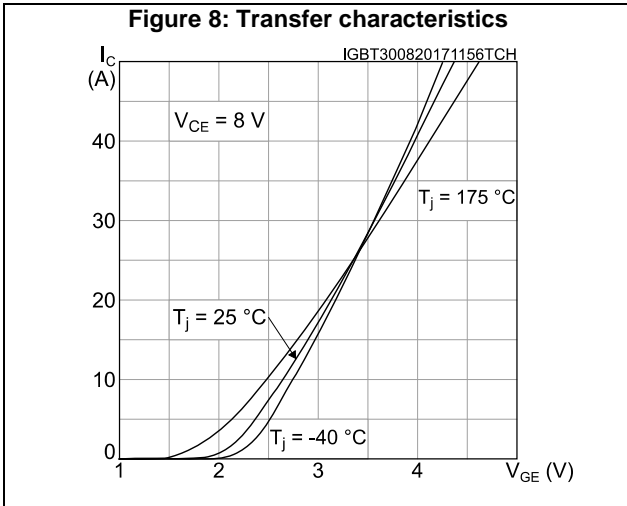
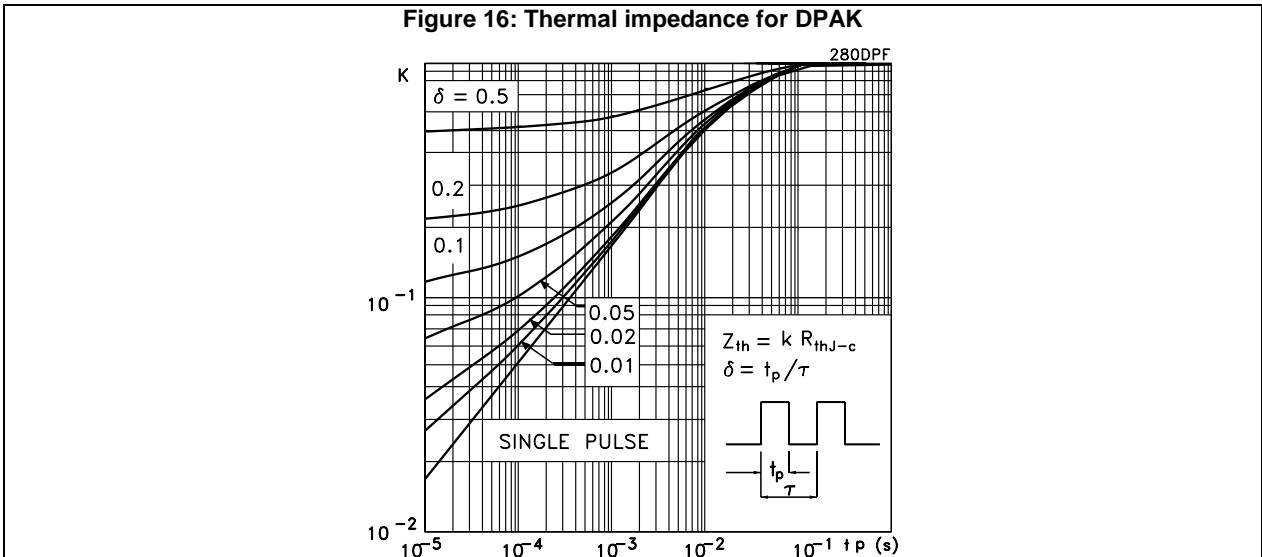
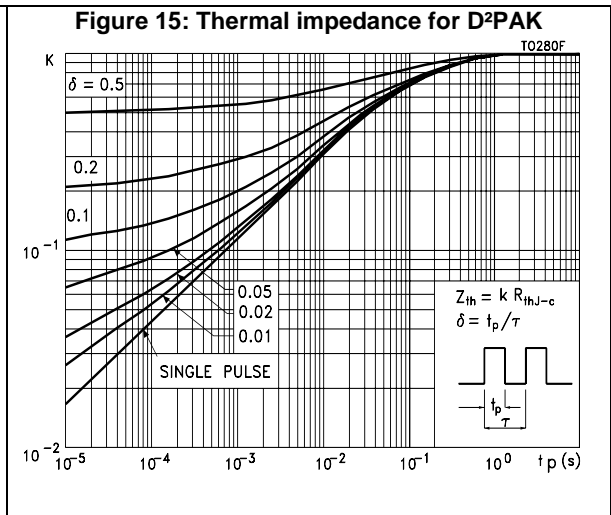
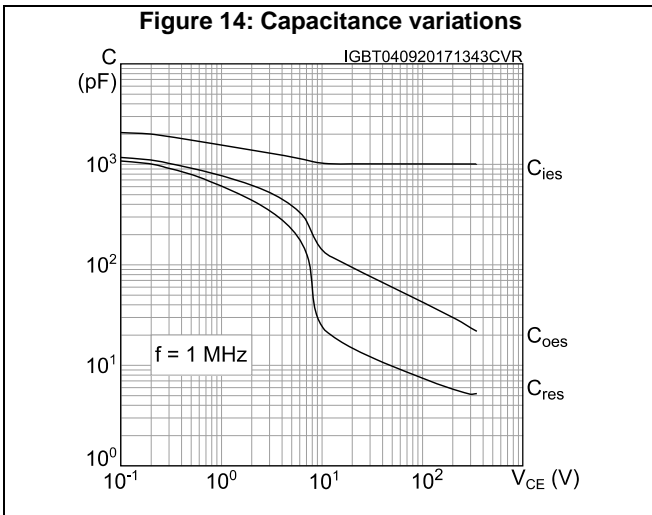


Figure 7: Output characteristics ($T_j = 175\text{ °C}$)

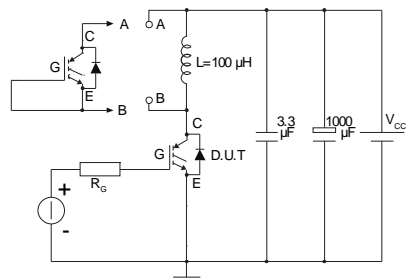






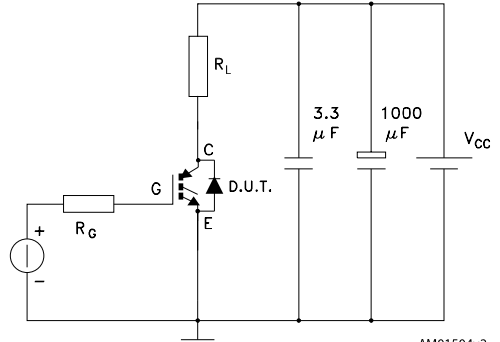
3 Test circuits

Figure 17: Test circuit for inductive load switching



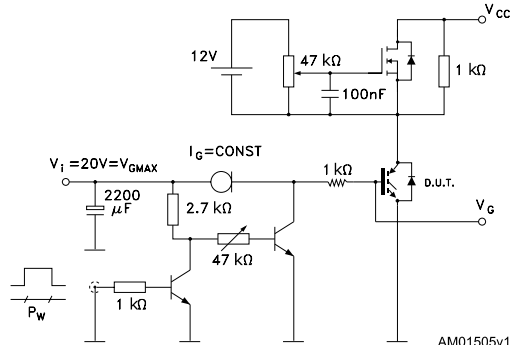
AM01504v1

Figure 18: Test circuit for resistive load switching



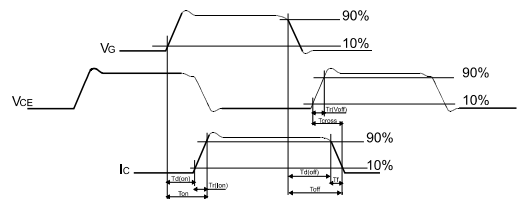
AM01504v2

Figure 19: Gate charge test circuit



AM01505v1

Figure 20: Switching waveform



AM01506v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 D²PAK (TO-263) type A package information

Figure 21: D²PAK (TO-263) type A package outline

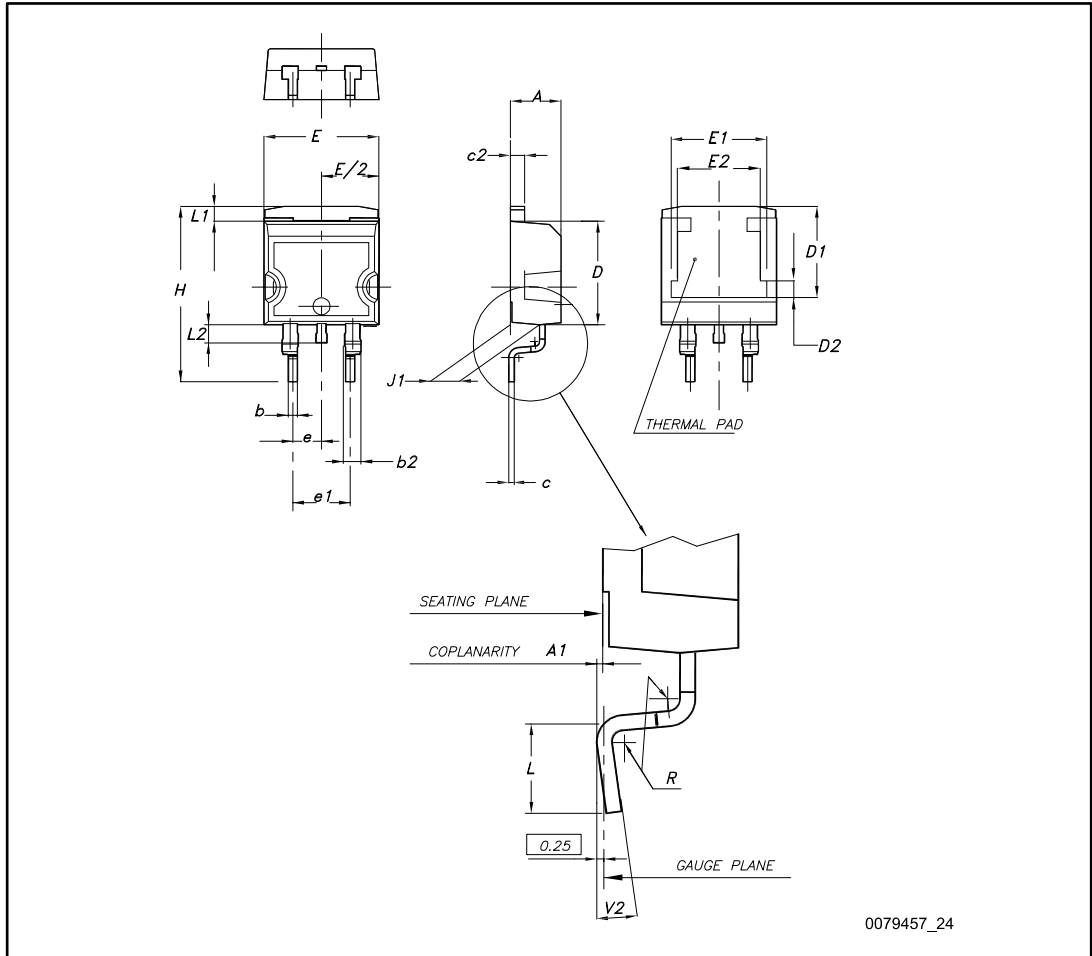
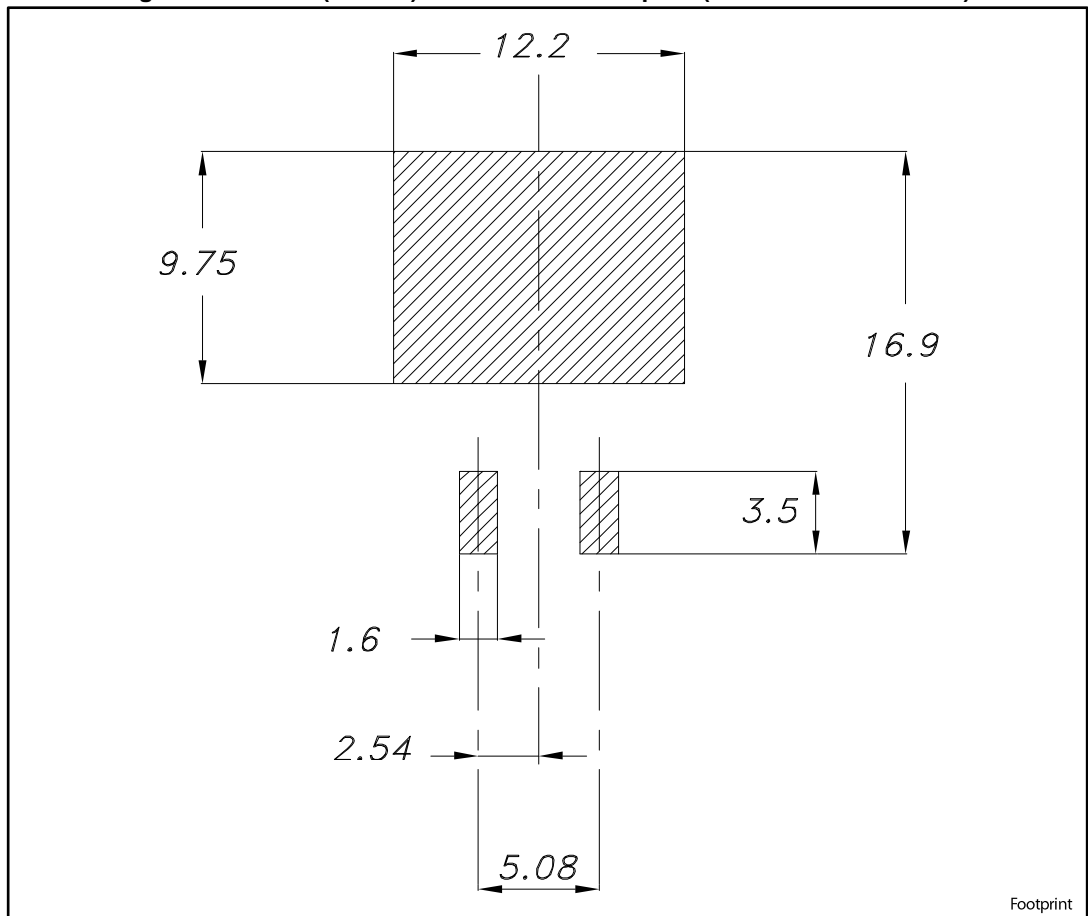


Table 8: D²PAK (TO-263) type A package mechanical data

| Dim. | mm | | |
|------|-------|------|-------|
| | Min. | Typ. | Max. |
| A | 4.40 | | 4.60 |
| A1 | 0.03 | | 0.23 |
| b | 0.70 | | 0.93 |
| b2 | 1.14 | | 1.70 |
| c | 0.45 | | 0.60 |
| c2 | 1.23 | | 1.36 |
| D | 8.95 | | 9.35 |
| D1 | 7.50 | 7.75 | 8.00 |
| D2 | 1.10 | 1.30 | 1.50 |
| E | 10.00 | | 10.40 |
| E1 | 8.50 | 8.70 | 8.90 |
| E2 | 6.85 | 7.05 | 7.25 |
| e | | 2.54 | |
| e1 | 4.88 | | 5.28 |
| H | 15.00 | | 15.85 |
| J1 | 2.49 | | 2.69 |
| L | 2.29 | | 2.79 |
| L1 | 1.27 | | 1.40 |
| L2 | 1.30 | | 1.75 |
| R | | 0.40 | |
| V2 | 0° | | 8° |

Figure 22: D²PAK (TO-263) recommended footprint (dimensions are in mm)



Footprint

4.2 DPAK (TO-252) type A2 package information

Figure 23: DPAK (TO-252) type A2 package outline

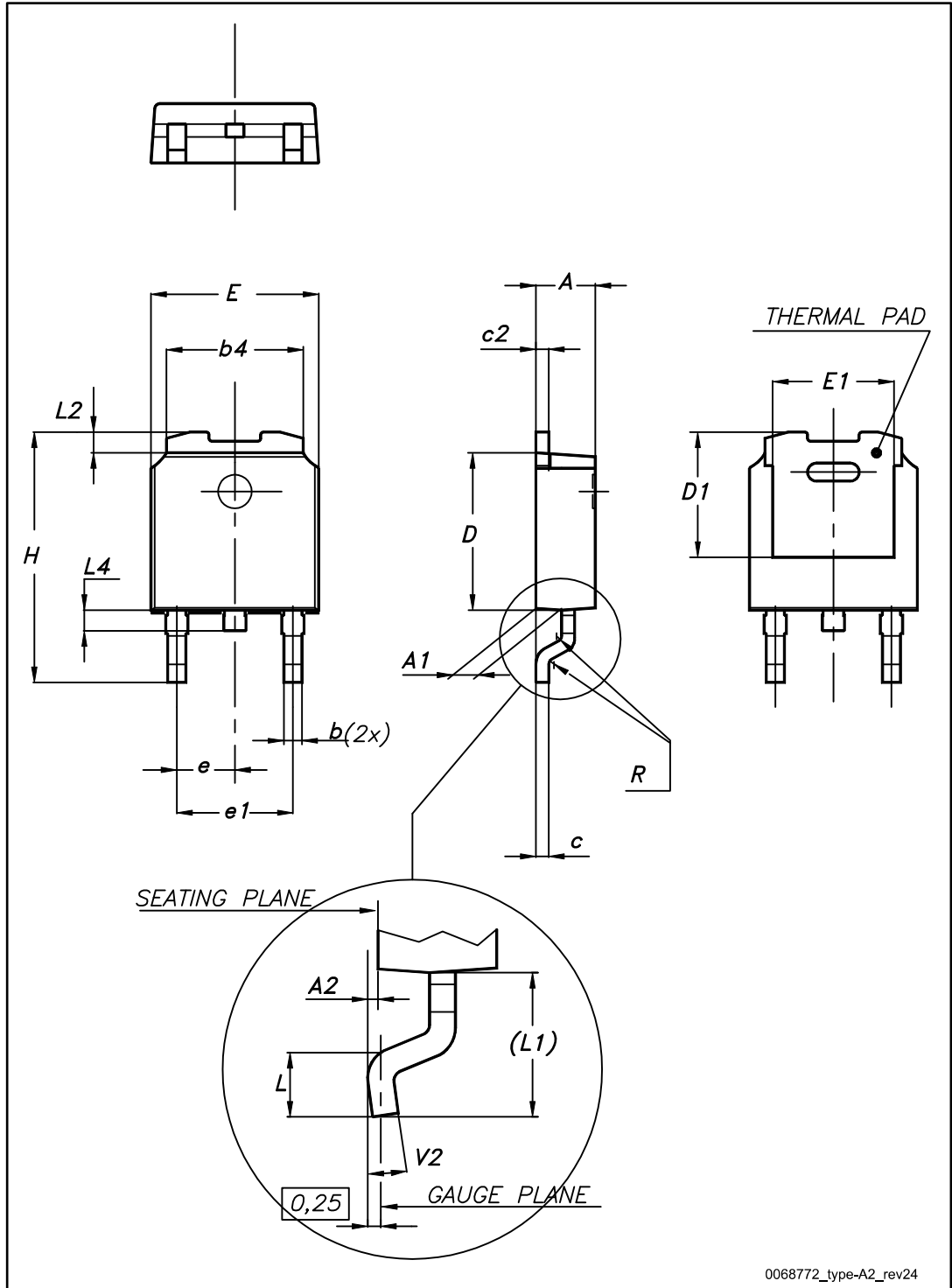
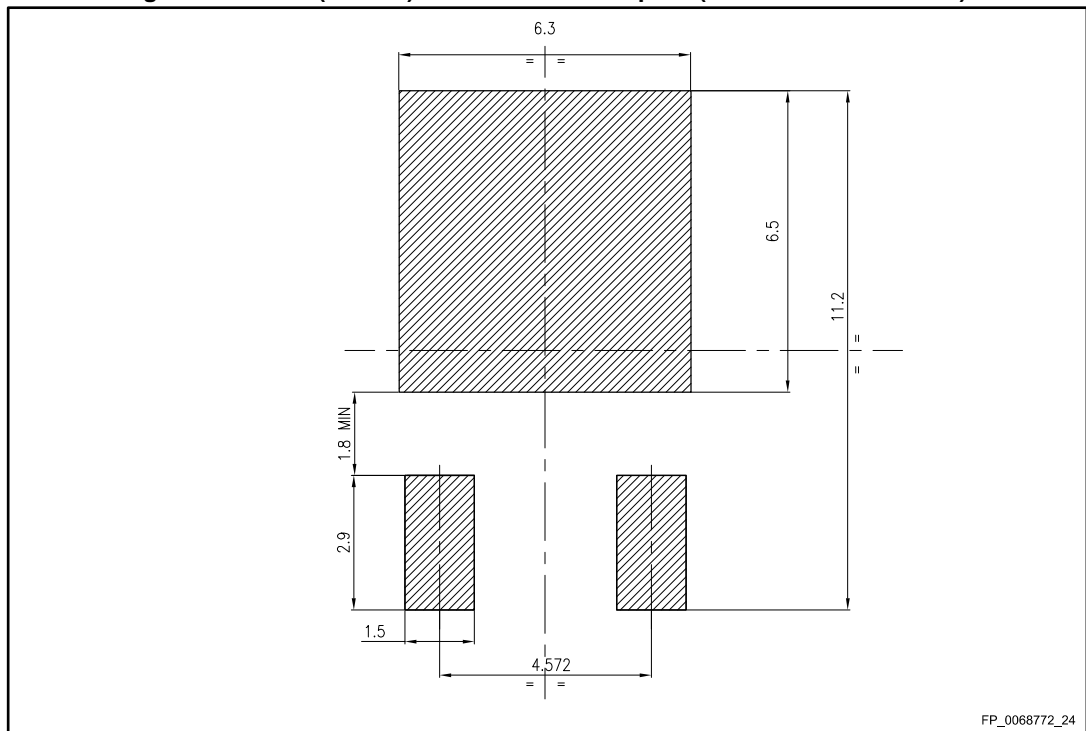


Table 9: DPAK (TO-252) type A2 mechanical data

| Dim. | mm | | |
|------|------|------|-------|
| | Min. | Typ. | Max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| A2 | 0.03 | | 0.23 |
| b | 0.64 | | 0.90 |
| b4 | 5.20 | | 5.40 |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| D1 | 4.95 | 5.10 | 5.25 |
| E | 6.40 | | 6.60 |
| E1 | 5.10 | 5.20 | 5.30 |
| e | 2.16 | 2.28 | 2.40 |
| e1 | 4.40 | | 4.60 |
| H | 9.35 | | 10.10 |
| L | 1.00 | | 1.50 |
| L1 | 2.60 | 2.80 | 3.00 |
| L2 | 0.65 | 0.80 | 0.95 |
| L4 | 0.60 | | 1.00 |
| R | | 0.20 | |
| V2 | 0° | | 8° |

Figure 24: DPAK (TO-252) recommended footprint (dimensions are in mm)



4.3 Packing information

Figure 25: Tape outline

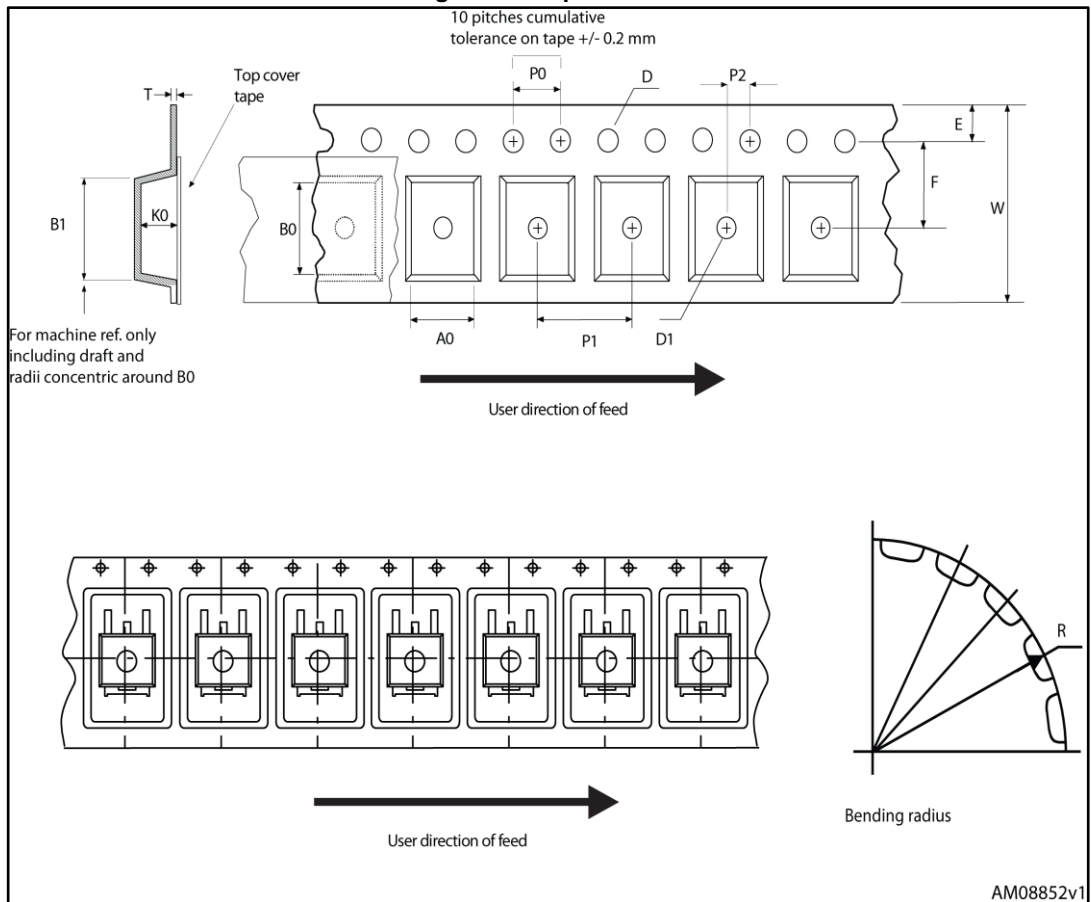
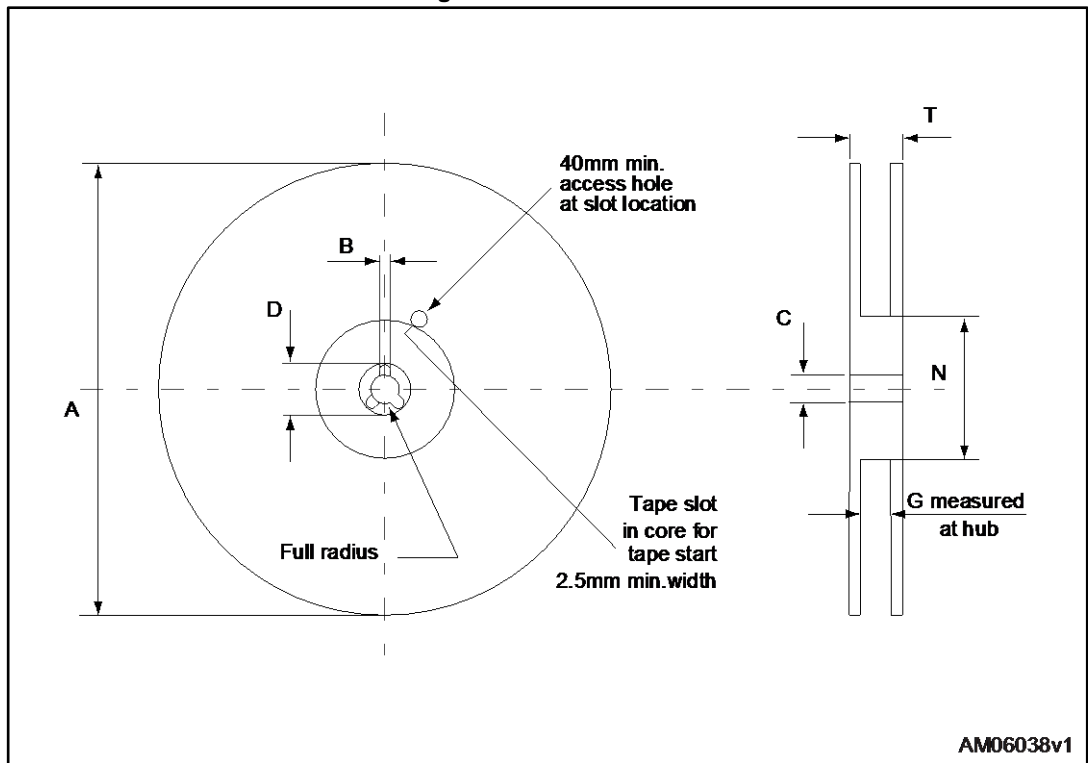


Figure 26: Reel outline



AM06038v1

Table 10: D²PAK tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|---------------|------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 10.5 | 10.7 | A | | 330 |
| B0 | 15.7 | 15.9 | B | 1.5 | |
| D | 1.5 | 1.6 | C | 12.8 | 13.2 |
| D1 | 1.59 | 1.61 | D | 20.2 | |
| E | 1.65 | 1.85 | G | 24.4 | 26.4 |
| F | 11.4 | 11.6 | N | 100 | |
| K0 | 4.8 | 5.0 | T | | 30.4 |
| P0 | 3.9 | 4.1 | | | |
| P1 | 11.9 | 12.1 | Base quantity | | 1000 |
| P2 | 1.9 | 2.1 | Bulk quantity | | 1000 |
| R | 50 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 23.7 | 24.3 | | | |

Table 11: DPAK tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|-----------|------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 6.8 | 7 | A | | 330 |
| B0 | 10.4 | 10.6 | B | 1.5 | |
| B1 | | 12.1 | C | 12.8 | 13.2 |
| D | 1.5 | 1.6 | D | 20.2 | |
| D1 | 1.5 | | G | 16.4 | 18.4 |
| E | 1.65 | 1.85 | N | 50 | |
| F | 7.4 | 7.6 | T | | 22.4 |
| K0 | 2.55 | 2.75 | | | |
| P0 | 3.9 | 4.1 | Base qty. | | 2500 |
| P1 | 7.9 | 8.1 | Bulk qty. | | 2500 |
| P2 | 1.9 | 2.1 | | | |
| R | 40 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 15.7 | 16.3 | | | |

5 Revision history

Table 12: Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 30-Oct-2015 | 1 | First release. |
| 01-Sep-2017 | 2 | Modified <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 3: "Thermal data"</i> , <i>Table 4: "Static characteristics"</i> and <i>Table 5: "Dynamic characteristics"</i> . Added <i>Section 2.1: "Electrical characteristics (curves)"</i> . Modified <i>Section 4: "Package information"</i> . Minor text changes. |
| 06-Sep-2017 | 3 | Modified <i>Figure 2: "$V_{CE(sat)}$ vs. junction temperature ($I_C = 6.0 A$)"</i> , <i>Figure 4: "Self clamped inductive switching current vs. inductance"</i> and <i>Figure 11: "Normalized $V_{CES(clamped)}$ vs. junction temperature"</i> . Minor text changes. |
| 11-Sep-2017 | 4 | Modified <i>Section 4.1: "D²PAK (TO-263) type A package information"</i> . Minor text changes. |
| 02-Nov-2017 | 5 | Updated <i>Table 4: "Static characteristics"</i> . Minor text changes |

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